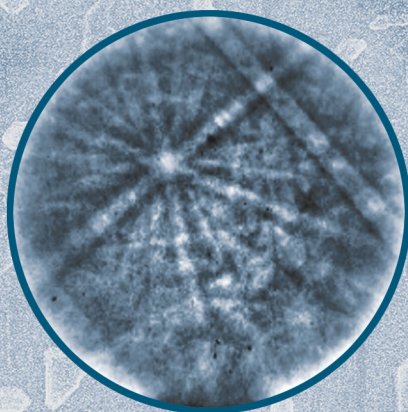




TiO



Ti₃O

Resistive switching phenomena of extended defects in Nb-doped SrTiO₃ under influence of external gradients

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Contents

Abstract	i
Kurzfassung	iii
1. Introduction	1
2. Basics	5
2.1. Crystal growth	5
2.2. Crystal structure	6
2.3. Defects	8
2.3.1. Point defects	8
2.3.2. Line defects	13
2.3.3. Two-dimensional defects	14
2.3.4. Secondary phases	15
2.3.5. Structure of the surface	20
2.4. Electronic structure	23
2.4.1. Electronic structure of the bulk	23
2.4.2. Electronic structure of the surface	30
2.5. Lattice dynamics	32
2.6. Transport properties and resistive switching	33
2.6.1. Electronic transport	33
2.6.2. Electroformation	34
2.6.3. Resistive switching	35
2.6.4. Resistive switching in SrTiO ₃ :Nb	38
3. Experimental methods	43
3.1. Preparation	43
3.1.1. Cleaving	43
3.1.2. Etching	43
3.1.3. Ar ⁺ bombardment	44

3.1.4. Electrodegradation	44
3.2. Characterization	44
3.2.1. Hardness measurement	45
3.2.2. X-ray diffraction (XRD)	46
3.2.3. X-ray topography (XRT)	46
3.2.4. Low energy electron diffraction (LEED)	47
3.2.5. Archimedes method	48
3.2.6. Laser flash analysis	48
3.2.7. Atomic force microscopy (AFM)	48
3.2.8. X-ray photoelectron spectroscopy (XPS)	52
3.2.9. Mass spectrometry	54
3.2.10. Fluorescence-lifetime imaging microscopy (FLIM)	55
3.2.11. Raman spectroscopy	56
3.2.12. Electrical four point measurements	57
3.2.13. Resistance and capacitance measurements	58
3.2.14. Electron microscopy	59
4. Results	61
4.1. Basic properties of the crystals	62
4.1.1. Colour and shape	62
4.1.2. Cleaving	62
4.1.3. Hardness	63
4.2. Crystallographic structure	64
4.2.1. Lattice constant	64
4.2.2. Structural imperfections	65
4.3. Chemical imperfections	69
4.3.1. Admixtures	69
4.3.2. Carbon contamination	70
4.4. Nb distribution	71
4.4.1. Nb distribution on the microscale	71
4.4.2. Nb distribution on the nanoscale	76
4.5. Surface layer	79
4.5.1. As-received surface layer	79
4.5.2. Bulk properties	81
4.5.3. Influence of different treatments on the surface layer	82
4.5.4. Simulation of the surface layer	87

4.5.5. Insulator-to-metal transition upon reduction	88
4.6. Influence of ion bombardment on the surface layer	96
4.6.1. Ar ⁺ bombardment	96
4.6.2. Atom probe measurements	104
4.7. Surface potential	106
4.7.1. Demonstration of the SKPM technique	106
4.7.2. Inhomogeneities in surface potential	110
4.7.3. Influence of annealing on the surface potential	113
4.8. Electronic transport phenomena of the surface layer	116
4.8.1. Influence of annealing under reducing conditions	116
4.8.2. Investigation of the conducting clusters by different surface prepa- rations	124
4.8.3. LC-AFM with atomic resolution	127
4.8.4. Theoretical investigation of Nb segregation	129
4.9. Resistive switching on the macroscale	131
4.9.1. Four-point measurements	132
4.9.2. Influence of oxidation	138
4.9.3. Influence of electrode preparation	140
4.10. Resistive switching on the nanoscale	141
4.10.1. Switching at a point-like contact	141
4.10.2. Switching of an area	143
4.10.3. Multi-level switching	146
4.10.4. Simulation of the cluster-like switching	146
4.11. Emulation of switching	150
4.11.1. Electrodegradation	150
4.11.2. Potential phase change model of resistive switching	162
5. Conclusions	169
Acknowledgements	195
Appendix	197
A. Four-probe set-up	197
B. Photographs of used setups	199



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